

P4C148, P4C149 ULTRA HIGH SPEED 1K x 4 STATIC CMOS RAMS



FEATURES

- Full CMOS, 6T Cell
- High Speed (Equal Access and Cycle Times)
 - 10/12/15/20/25/35/45/55 ns (Commercial)
 - 15/20/25/35/45/55 ns
- Low Power Operation
- Single 5V ± 10% Power Supply
- Two Options
 - P4C148 Low Power Standby Mode
 - P4C149 Fast Chip Select Control
- Common Input/Output Ports
- Three-State Outputs
- Fully TTL Compatible Inputs and Outputs
- Standard Pinout (JEDEC Approved)
 - 18 Pin 300 mil DIP
 - 18 Pin LCC (295 x 335 mil) [P4C148 only]
 - 18 Pin LCC (290 x 430 mil)



DESCRIPTION

The P4C148 and P4C149 are 4,096-bit ultra high-speed static RAMs organized as 1K x 4. Both devices have common input/output ports. The P4C148 enters the standby mode when the chip enable (\overline{CE}) goes HIGH; with CMOS input levels, power consumption is extremely low in this mode. The P4C149 features a fast chip select capability using \overline{CS} . The CMOS memories require no clocks or refreshing, and have equal access and cycle times. Inputs are fully TTL-compatible. The RAMs operate from a single 5V ± 10% tolerance power supply.

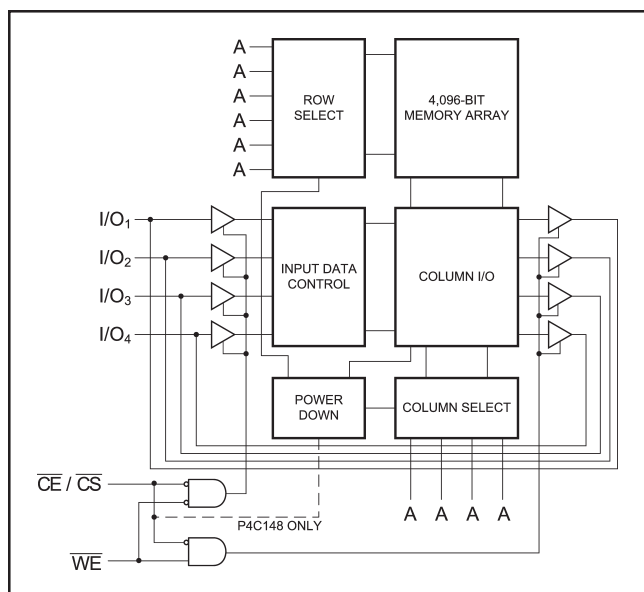
Access times as fast as 10 nanoseconds are available, permitting greatly enhanced system operating speeds.

CMOS is used to reduce power consumption when active; for the P4C148, consumption is further reduced in the standby mode.

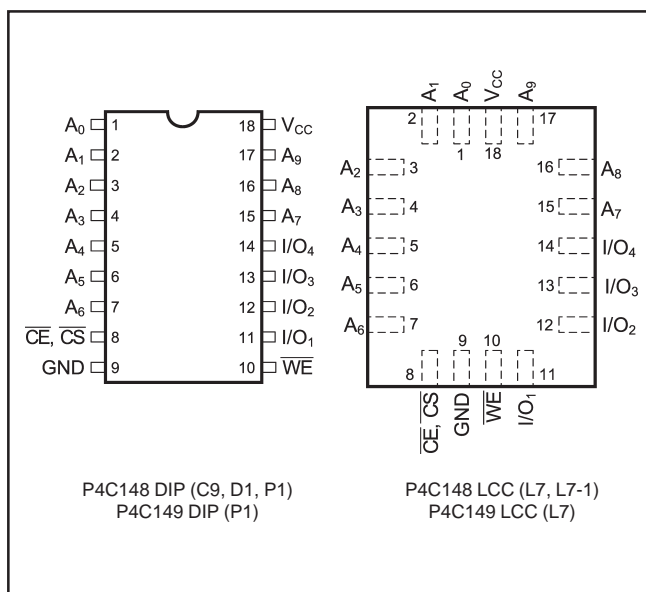
The P4C148 and P4C149 are available in 18-pin 300 mil DIP packages, as well as 2 different LCC packages, providing excellent board level densities.



FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V _{CC}	Power Supply Pin with Respect to GND	-0.5 to +7	V
V _{TERM}	Terminal Voltage with Respect to GND (up to 7.0V)	-0.5 to V _{CC} +0.5	V
T _A	Operating Temperature	-55 to +125	°C

Symbol	Parameter	Value	Unit
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _T	Power Dissipation	1.0	W
I _{OUT}	DC Output Current	50	mA

RECOMMENDED OPERATING CONDITIONS

Grade ⁽²⁾	Ambient Temp	Gnd	V _{CC}
Commercial	0°C to 70°C	0V	5.0V ± 10%
Military	-55°C to +125°C	0V	5.0V ± 10%

CAPACITANCES⁽⁴⁾

(V_{CC} = 5.0V, T_A = 25°C, f = 1.0MHz)

Symbol	Parameter	Conditions	Typ.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	5	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	7	pF

DC ELECTRICAL CHARACTERISTICS

Over recommended operating temperature and supply voltage (2)

Sym.	Parameter	Test Conditions	P4C148		P4C149		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output High Voltage (TTL Load)	I _{OH} = -4 mA, V _{CC} = Min.	2.4		2.4		V
V _{OL}	Output Low Voltage (TTL Load)	I _{OL} = +8 mA, V _{CC} = Min		0.4		0.4	V
V _{IH}	Input High Voltage		2.2	V _{CC} +0.5	2.2	V _{CC} +0.5	V
V _{IL}	Input Low Voltage		-0.5 ⁽³⁾	0.8	-0.5 ⁽³⁾	0.8	V
I _{LI}	Input Leakage Current	V _{CC} = Max., V _{IN} = GND to V _{CC}	Mil. Comm'l -10 -5	+10 +5	-10 -5	+10 +5	µA
I _{LO}	Output Leakage Current	V _{CC} = Max., $\overline{CE}, \overline{CS} = V_{IH}$, V _{OUT} = GND to V _{CC}	Mil. Comm'l -10 -5	+10 +5	-10 -5	+10 +5	µA
I _{SB}	Standby Power Supply Current (TTL Input Levels)	$\overline{CE} \geq V_{IH}$, V _{CC} = Max., f=Max., Outputs Open	Mil. Comm'l	30 23		N/A N/A	mA
I _{SB1}	Standby Power Supply Current (CMOS Input Levels)	$\overline{CE} \geq V_{HC}$, V _{CC} = Max., f= 0, Outputs Open V _{IN} ≤ 0.2V or V _{IN} ≥ V _{CC} -0.2V	Mil. Comm'l	15 10		N/A N/A	mA

N/A = Not Applicable

POWER DISSIPATION CHARACTERISTICS VS. SPEED

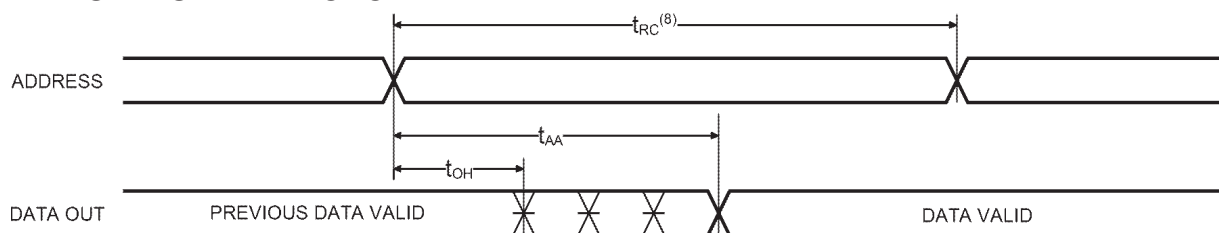
Symbol	Parameter	Temperature Range	-10	-12	-15	-20	-25	-35	-45	-55	Unit
I _{CC}	Dynamic Operating Current	Commercial	130	130	120	115	100	100	95	95	mA
		Military	N/A	N/A	145	135	125	120	115	115	mA

AC CHARACTERISTICS—READ CYCLE

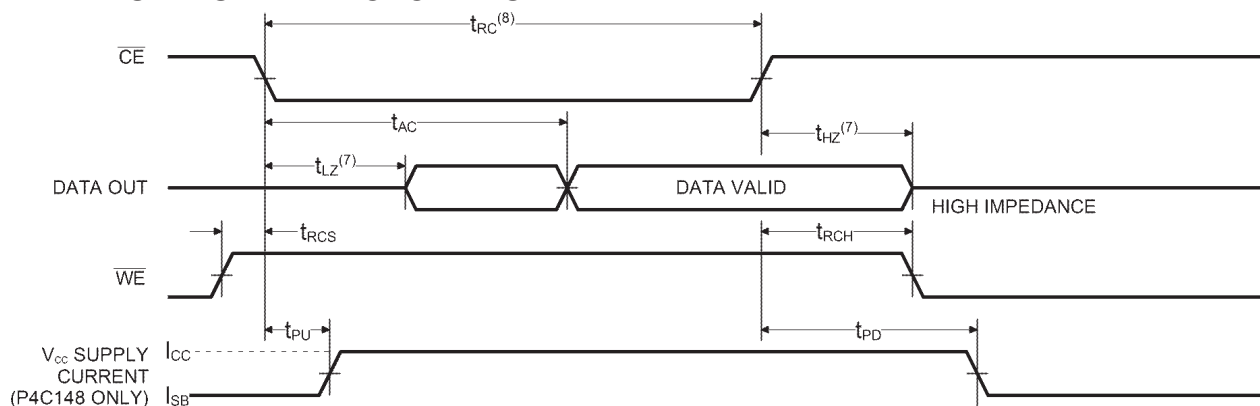
($V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

Sym	Parameter	-10		-12		-15		-20		-25		-35		-45		-55	
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
t_{RC}	Read Cycle Time	10		12		15		20		25		35		45		55	
t_{AA}	Address Access Time		10		12		15		20		25		35		45		55
t_{AC}	Chip Enable Access Time (P4C148)		10		12		15		20		25		35		45		55
t_{AC}	Chip Enable Access Time (P4C149)		8		10		12		14		15		20		20		25
t_{OH}	Output Hold from Address Change	3		3		3		3		3		3		3		3	
t_{LZ}	Chip Enable to Output in Low Z (P4C149)	2		2		2		2		2		2		2		2	
t_{HZ}	Chip Disable to Output in High Z (P4C149)		4		5		6		8		10		14		18		20
t_{RCS}	Read Command Setup Time	0		0		0		0		0		0		0		0	
t_{RCH}	Read Command Hold Time	0		0		0		0		0		0		0		0	
t_{PU}	Chip Enable to Power Up Time (P4C148)	0		0		0		0		0		0		0		0	
t_{PD}	Chip Disable to Power Down Time (P4C148)		10		12		15		20		25		35		45		55

TIMING WAVEFORM OF READ CYCLE



TIMING WAVEFORM OF READ CYCLE NO. 2⁽⁶⁾



Notes:

- Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to MAXIMUM rating conditions for extended periods may affect reliability.
- Extended temperature operation guaranteed with 400 linear feet per minute of air flow.
- Transient inputs with V_L and I_L not more negative than $-3.0V$ and

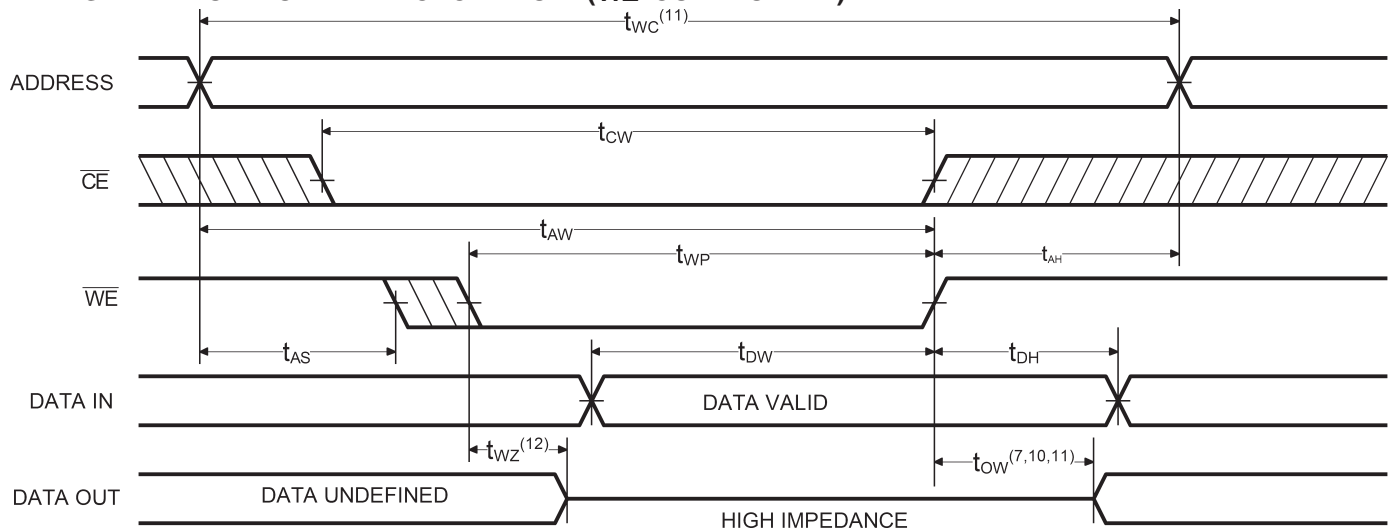
- $-100mA$, respectively, are permissible for pulse widths up to 20ns.
- This parameter is sampled and not 100% tested.
- \overline{CE} is LOW and \overline{WE} is HIGH for READ cycle.
- \overline{WE} is HIGH, and address must be valid prior to or coincident with \overline{CE} transition LOW.
- Transition is measured $\pm 200mV$ from steady state voltage prior to change with specified loading in Figure 1. This parameter is sampled and not 100% tested.
- Read Cycle Time is measured from the last valid address to the first transitioning address.

AC CHARACTERISTICS—WRITE CYCLE

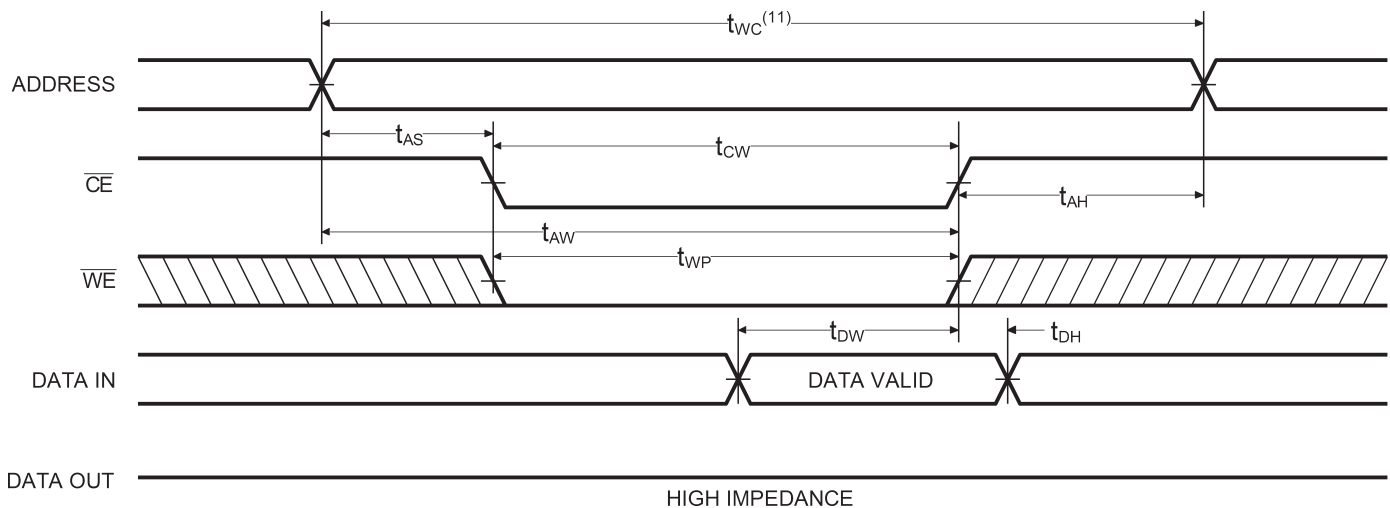
($V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

Sym	Parameter	-10		-12		-15		-20		-25		-35		-45		-55	
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
t_{WC}	Write Cycle Time	10		12		15		20		25		35		45		55	
t_{CW}	Chip Enable Time to End of Write	8		10		12		16		20		25		30		35	
t_{AW}	Address Valid to End of Write	8		10		12		16		20		25		30		35	
t_{AS}	Address Set-up Time	0		0		0		0		0		0		0		0	
t_{WP}	Write Pulse Width	8		10		12		16		20		25		30		35	
t_{AH}	Address Hold Time from End of Write	0		0		0		0		0		0		0		0	
t_{DW}	Data Valid to End of Write	5		6		7		9		12		16		20		25	
t_{DH}	Data Hold Time	0		0		0		0		0		0		0		0	
t_{WZ}	Write Enable to Output in High Z		5		6		7		7		8		12		15		20
t_{OW}	Output Active from End of Write	0		0		0		0		0		0		0		0	

TIMING WAVEFORM OF WRITE CYCLE NO. 1 (\overline{WE} CONTROLLED)⁽⁹⁾



TIMING WAVEFORM OF WRITE CYCLE NO. 2 ($\overline{CE}/\overline{CS}$ CONTROLLED)⁽⁹⁾



Notes:

- \overline{CE} and \overline{WE} must be LOW for WRITE cycle.
- If \overline{CE} goes HIGH simultaneously with \overline{WE} high, the output remains in a high impedance state.
- Write Cycle Time is measured from the last valid address to the first transition address.

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise and Fall Times	3ns
Input Timing Reference Level	1.5V
Output Timing Reference Level	1.5V
Output Load	See Figures 1 and 2

TRUTH TABLE

Mode	\overline{CE}	\overline{WE}	Output	Power
Standby	H	X	High Z	Standby
Read	L	H	D _{OUT}	Active
Write	L	L	High Z	Active

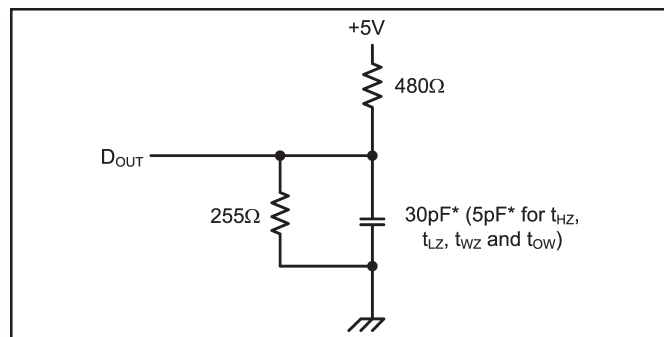


Figure 1. Output Load

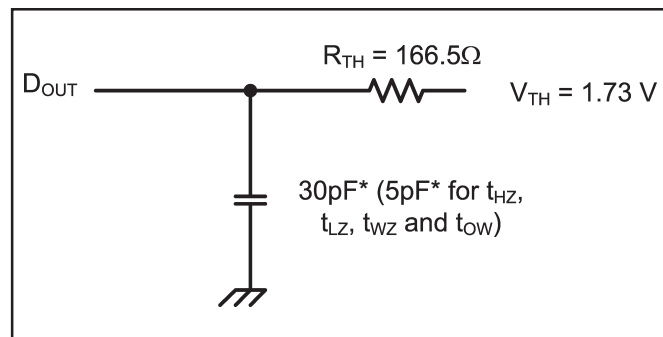


Figure 2. Thevenin Equivalent

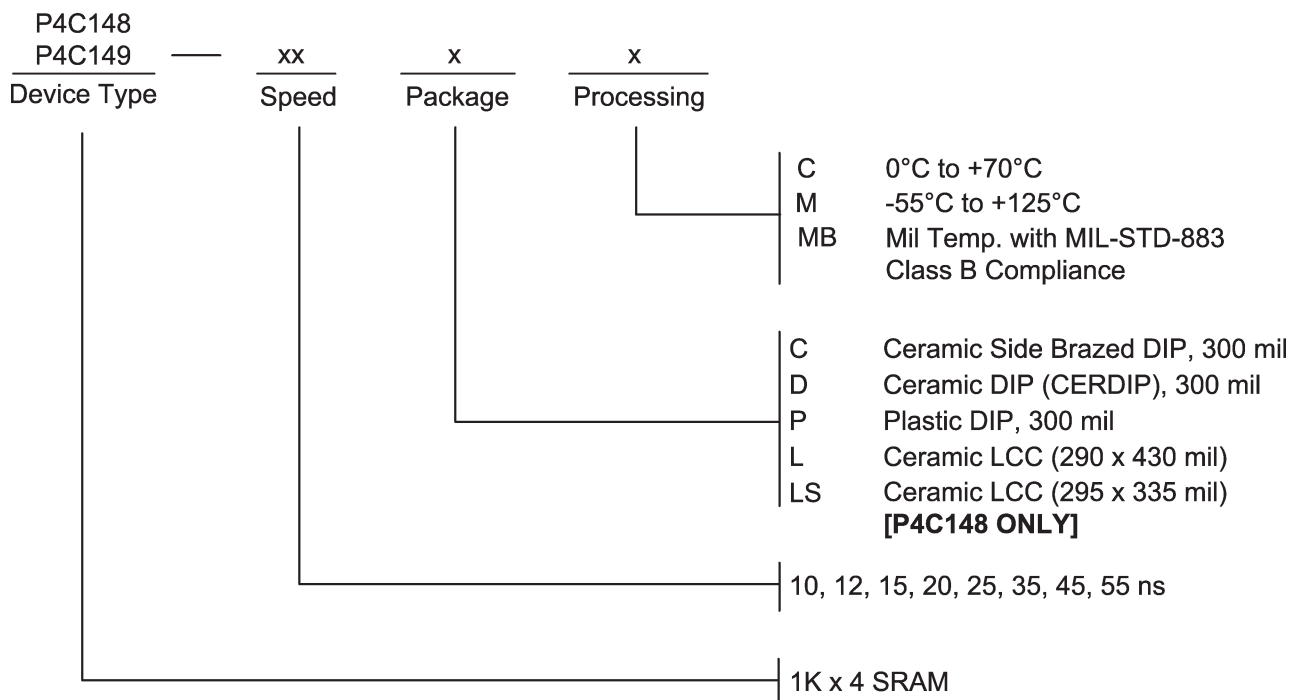
* including scope and test fixture.

Note:

Due to the ultra-high speed of the P4C148/149, care must be taken when testing this device; an inadequate setup can cause a normal functioning part to be rejected as faulty. Long high-inductance leads that cause supply bounce must be avoided by bringing the V_{CC} and ground planes directly up to the contactor fingers. A 0.01 μF high frequency

capacitor is also required between V_{CC} and ground. To avoid signal reflections, proper termination must be used; for example, a 50Ω test environment should be terminated into a 50Ω load with 1.73V (Thevenin Voltage) at the comparator input, and a 116Ω resistor must be used in series with D_{OUT} to match 166Ω (Thevenin Resistance).

ORDERING INFORMATION



SELECTION GUIDE

The P4C148/P4C149 are available in the following temperature, speed and package options.

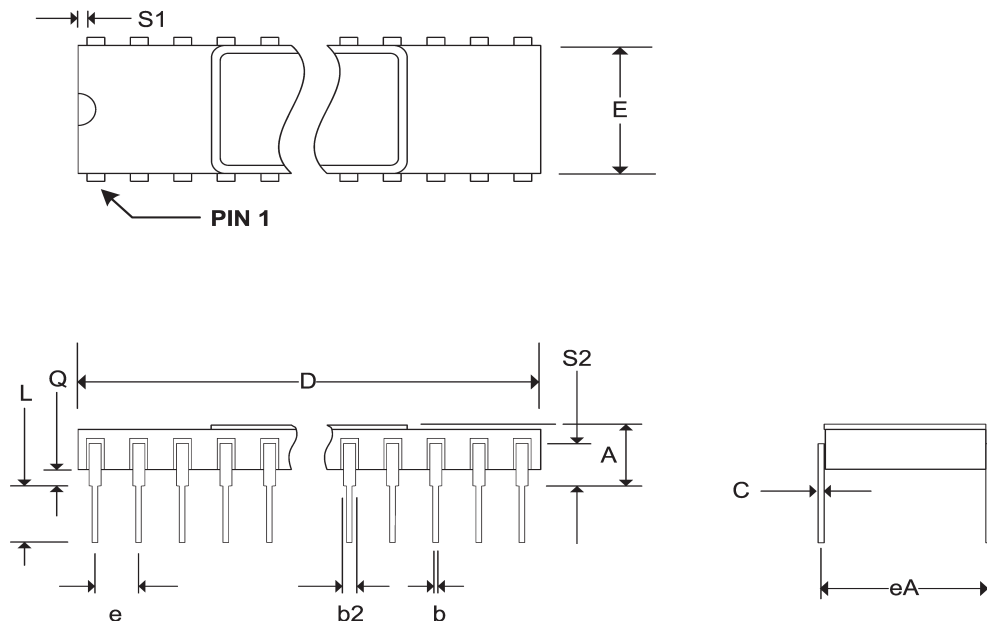
Temperature Range	Package	Speed (ns)							
		10	12	15	20	25	35	45	55
Commercial Temperature	Plastic DIP	-10PC	-12PC	-15PC	-20PC	-25PC	-35PC	-45PC	-55PC
	Side Brazed DIP	-10CC	-12CC	-15CC	-20CC	-25CC	-35CC	-45CC	-55CC
Military Temperature	CERDIP	N/A	N/A	-15DM	-20DM	-25DM	-35DM	-45DM	-55DM
	Side Brazed DIP	N/A	N/A	-15CM	-20CM	-25CM	-35CM	-45CM	-55CM
	LCC (290 x 430 mil)	N/A	N/A	-15LM	-20LM	-25LM	-35LM	-45LM	-55LM
	LCC (295 x 335 mil)	N/A	N/A	-15LSM	-20LSM	-25LSM	-35LSM	-45LSM	-55LSM
Military Processed*	CERDIP	N/A	N/A	-15DMB	-20DMB	-25DMB	-35DMB	-45DMB	-55DMB
	Side Brazed DIP	N/A	N/A	-15CMB	-20CMB	-25CMB	-35CMB	-45CMB	-55CMB
	LCC (290 x 430 mil)	N/A	N/A	-15LMB	-20LMB	-25LMB	-35LMB	-45LMB	-55LMB
	LCC (295 x 335 mil)	N/A	N/A	-15LSMB	-20LSMB	-25LSMB	-35LSMB	-45LSMB	-55LSMB

* Military temperature range with MIL-STD-883, Class B processing.

N/A = Not Available

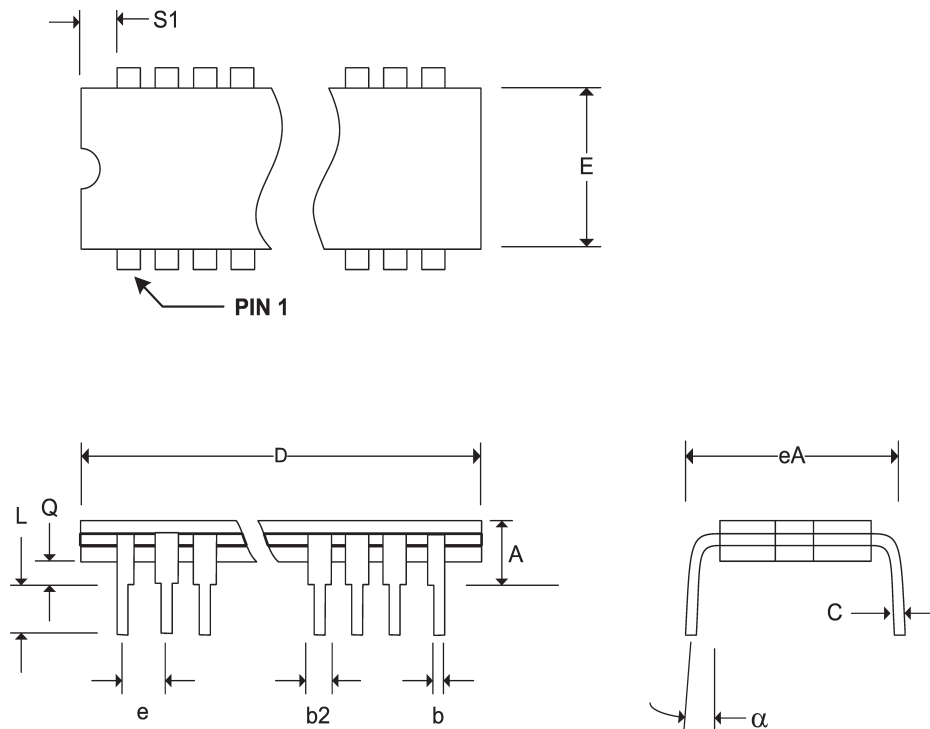
Pkg #	C9	
# Pins	18 (300 Mil)	
Symbol	Min	Max
A	-	0.200
b	0.014	0.026
b2	0.030	0.065
C	0.008	0.018
D	-	0.960
E	0.220	0.320
eA	0.300 BSC	
e	0.100 BSC	
L	0.125	0.200
Q	0.015	0.070
S1	0.005	-
S2	0.005	-

SIDE BRAZED DUAL IN-LINE PACKAGES



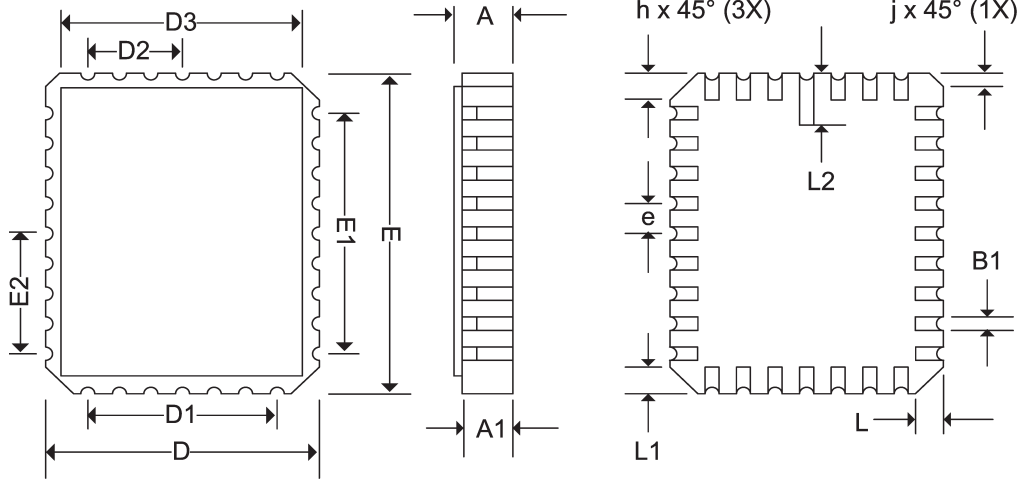
Pkg #	D1	
# Pins	18 (300 Mil)	
Symbol	Min	Max
A	-	0.200
b	0.014	0.026
b2	0.045	0.065
C	0.008	0.018
D	-	0.960
E	0.220	0.310
eA	0.300 BSC	
e	0.100 BSC	
L	0.125	0.200
Q	0.015	0.070
S1	0.005	-
α	0°	15°

CERDIP DUAL IN-LINE PACKAGES



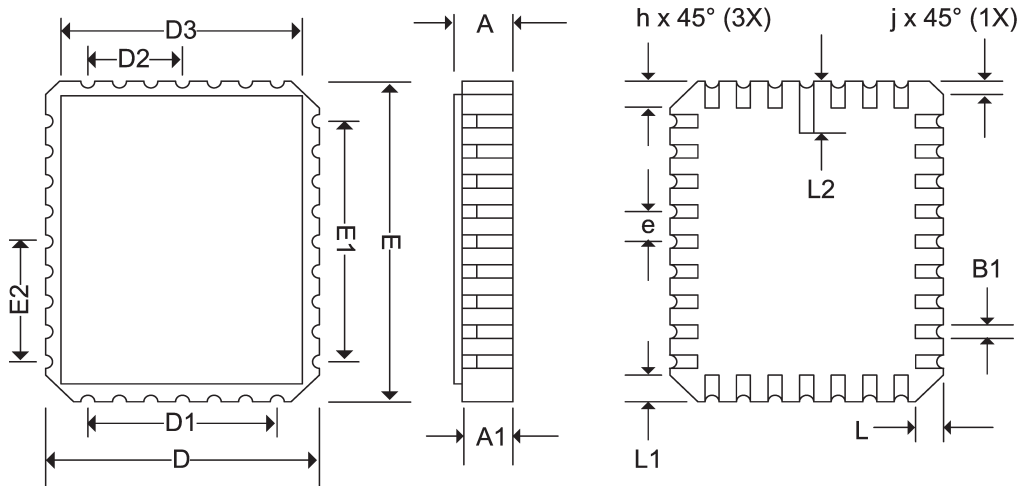
Pkg #	L7	
# Pins	18	
Symbol	Min	Max
A	0.060	0.075
A1	0.050	0.065
B1	0.022	0.028
D	0.280	0.305
D1	.150 BSC	
D2	.075 BSC	
D3	-	0.305
E	0.417	0.440
E1	0.200 BSC	
E2	0.100 BSC	
E3	-	0.440
e	0.050 BSC	
h	0.040 REF	
j	0.020 REF	
L	0.045	0.055
L1	0.075	0.090
L2	0.075	0.148
ND	4	
NE	5	

RECTANGULAR LEADLESS CHIP CARRIER



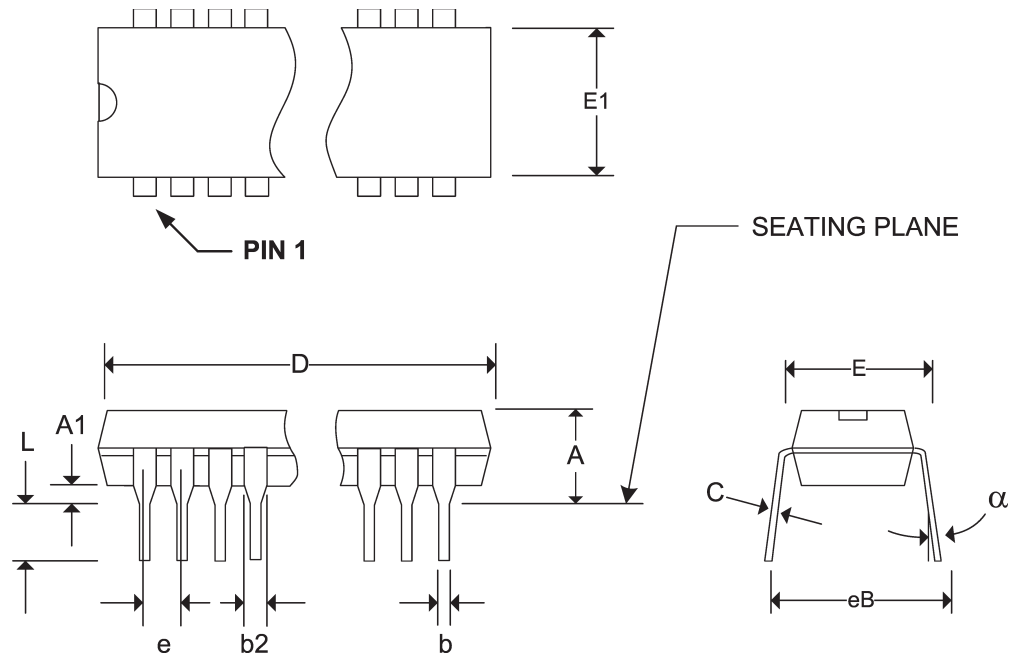
Pkg #	L7-1	
# Pins	18	
Symbol	Min	Max
A	0.060	0.075
A1	0.050	0.065
B1	0.022	0.028
D	0.280	0.305
D1	.150 BSC	
D2	.075 BSC	
D3	-	0.305
E	0.345	0.365
E1	0.200 BSC	
E2	0.100 BSC	
E3	-	0.365
e	0.050 BSC	
h	0.040 REF	
j	0.020 REF	
L	0.045	0.055
L1	0.045	0.055
L2	0.075	0.125
ND	4	
NE	5	

RECTANGULAR LEADLESS CHIP CARRIER (SMALL)



Pkg #	P1	
# Pins	18 (300 Mil)	
Symbol	Min	Max
A	-	0.210
A1	0.015	-
b	0.014	0.022
b2	0.045	0.070
C	0.008	0.014
D	0.880	0.920
E1	0.240	0.280
E	0.300	0.325
e	0.100 BSC	
eB	-	0.430
L	0.115	0.150
α	0°	15°

PLASTIC DUAL IN-LINE PACKAGE



REVISIONS

DOCUMENT NUMBER:		SRAM104	
DOCUMENT TITLE:		P4C148/P4C149 ULTRA HIGH SPEED 1K x 4 STATIC CMOS RAMS	
REV.	ISSUE DATE	ORIG. OF CHANGE	DESCRIPTION OF CHANGE
OR	1997	DAB	New Data Sheet
A	Oct-05	JDB	Change logo to Pyramid
B	Apr-07	JDB	Added 45 and 55 ns speeds
C	Nov-07	JDB	Removed reference to P4C148 Military from cover page